	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	160	"5286344"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:39			
2	BRS	L2	15258	((wet etch$3) or etch$3) same ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2")) same ("contact hole" or contact or hole or node or nodal or SAC or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:45			
3	BRS	L3	9766	2 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:47			
4	BRS	L4	9710	((etch$3) same ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2"))) same ("contact hole" or hole or node or nodal or SAC or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:25			
5	BRS	L5	6093	4 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:50			
6	BRS	L6	3264	5 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:50			
7	BRS	L7	2462	((etch$3) same ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2"))) same ("contact hole" or hole or node or nodal or SAC or (self adj align$4)) same (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 11:15			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L8	1627	7 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 11:18			
9	BRS	L10	11	8 and 438/745	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 10:51			
10	BRS	L9	973	8 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 11:25			
11	BRS	L11	843	(((etch$3) not (plasma or gas)) same ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2"))) same ("contact hole" or hole or node or nodal or SAC or (self adj align$4)) same (source and drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 11:16			
12	BRS	L12	616	11 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:30			
13	BRS	L13	261	12 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:31			
14	BRS	L14	9794	((wet etch$3) same ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2"))) same ("contact hole" or hole or node or nodal or SAC or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:29			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
15	BRS	L15	4952	((wet etch$3) with ((SiN or Si3N4 or "silicon nitride" or "Si.sub.3N.sub.4") same (oxide or SiO2 or "silicon dioxide" or"SiO.sub.2"))) same ("contact hole" or hole or node or nodal or SAC or (self adj align$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:35			
16	BRS	L16	3172	15 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:38			
17	BRS	L17	1820	16 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:39			
18	BRS	L18	1784	15 not ("dry etching" or "plasma etching" or rie or "reactive ion etching")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:35			
19	BRS	L19	1265	18 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:38			
20	BRS	L20	596	19 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 13:39			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	32	(etch$3) with (nitride or SiN or Si3N4 or "Si.sub.3N.sub.4") with (phosphoric or H3PO4 or "H.sub.3PO.sub.4") with ("%" or percent$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:08			
2	BRS	L2	19	1 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:08			
3	BRS	L3	504	(etch$3) with (phosphoric or H3PO4 or "H.sub.3PO.sub.4") with ("%" or percent$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:14			
4	BRS	L4	363	3 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:15			
5	BRS	L5	90	4 and "438"/$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:10			
6	BRS	L6	25	(etch$3) with (phosphoric or H3PO4 or "H.sub.3PO.sub.4") with ("%" or percent$3) with (known or conventional)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:14			
7	BRS	L7	25	6 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/13 18:15			